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# 2SJ218

Silicon P-Channel MOS FET

# HITACHI

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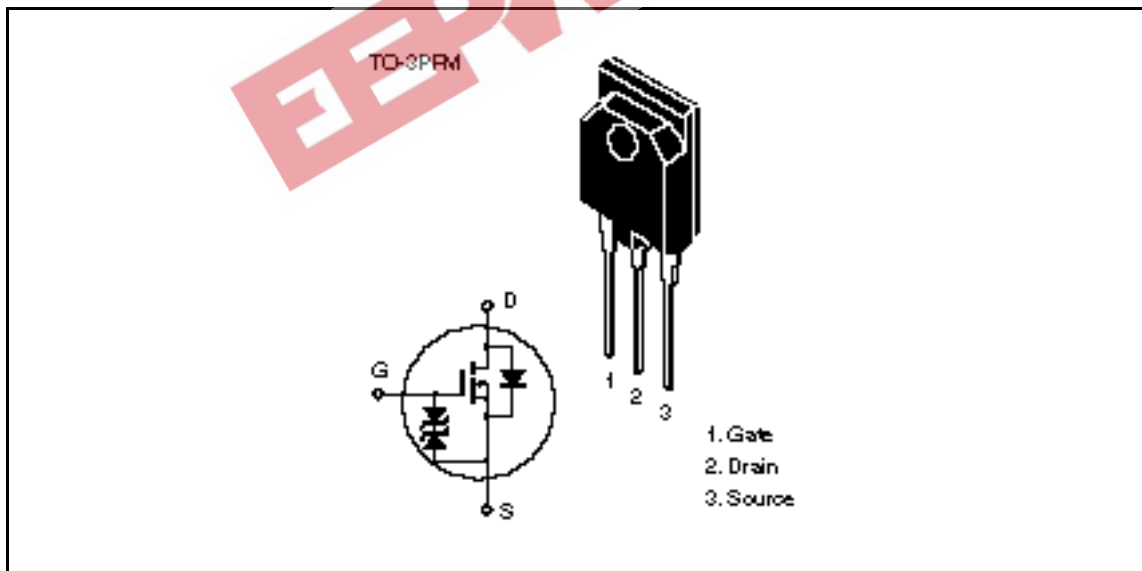
## Application

High speed power switching

## Features

- Low on-resistance
- High speed switching
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

## Outline



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### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	-45	A
Drain peak current	$I_{D(pulse)}^{*1}$	-180	A
Body to drain diode reverse drain current	$I_{DR}$	-45	A
Channel dissipation	$P_{ch}^{*2}$	60	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10 μs, duty cycle 1%  
2. Value at T<sub>c</sub> = 25°C

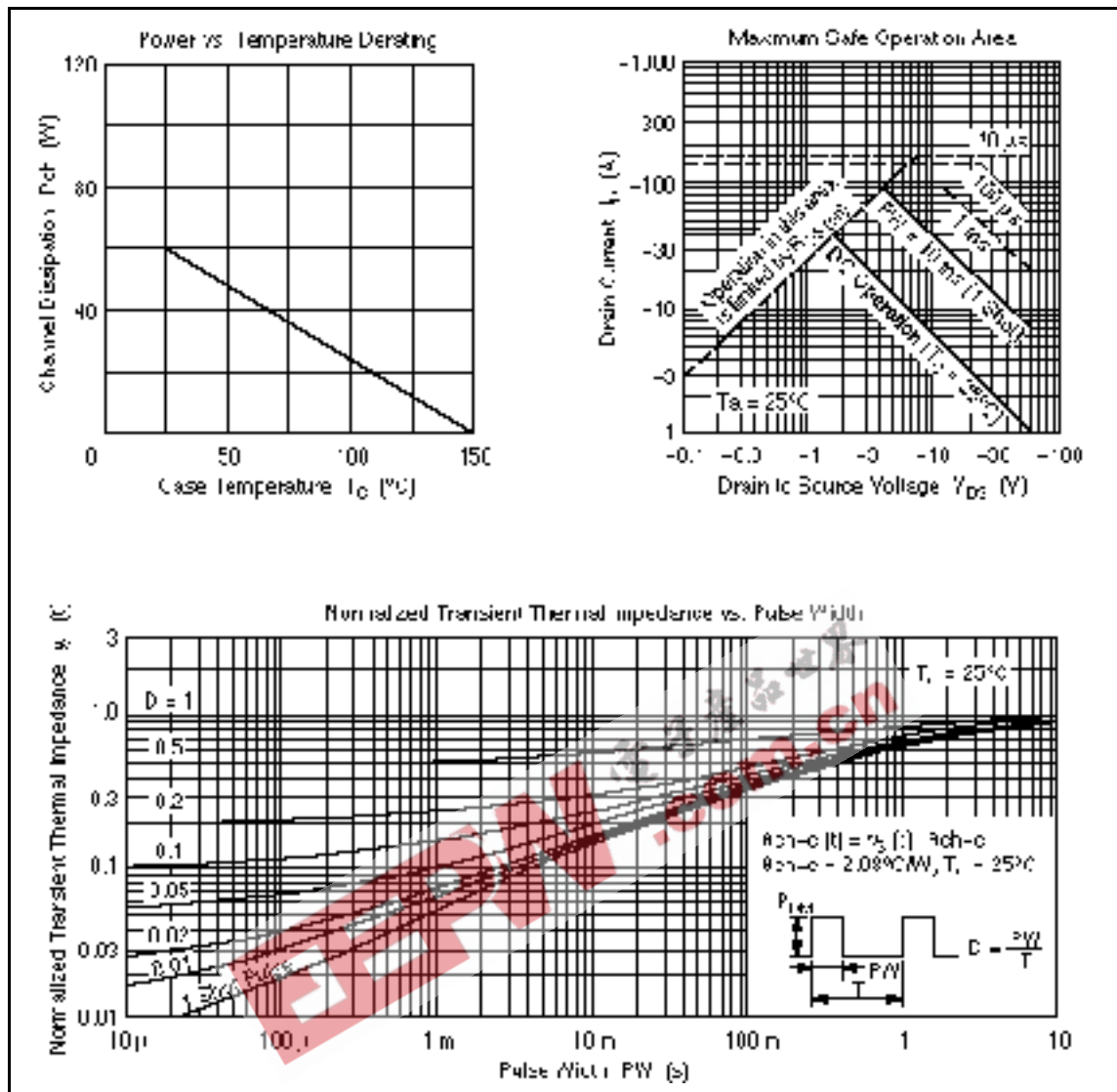
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## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-250	$\mu\text{A}$	$V_{DS} = -50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.033	0.042		$I_D = -20 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$
		—	0.045	0.06		$I_D = -20 \text{ A}, V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	16	25	—	S	$I_D = -20 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	3800	—	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	$C_{oss}$	—	2000	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	—	490	—	pF	
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = -20 \text{ A}, V_{GS} = -10 \text{ V},$
Rise time	$t_r$	—	235	—	ns	$R_L = 1.5$
Turn-off delay time	$t_{d(off)}$	—	670	—	ns	
Fall time	$t_f$	—	450	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	-1.35	—	V	$I_F = -45 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	300	—	ns	$I_F = -45 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

See characteristic curves of 2SJ217



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# HITACHI

## Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-5-2, Ohta-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.  
Semiconductor & IC Div.  
2000 Sierra Point Parkway  
Brisbane, CA 94005-4835  
U.S.A.  
Tel: 415-589-8000  
Fax: 415-589-4207

Hitachi Europe GmbH  
Electronic Components Group  
Continental Europe  
Dornacher Straße 3  
D-85622 Feldkirchen  
München  
Tel: 089-9 94 80-0  
Fax: 089-9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Div.  
Northern Europe Headquarters  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA  
United Kingdom  
Tel: 0628-585000  
Fax: 0628-778322

Hitachi Asia Pte. Ltd.  
45 Collyer Quay #20-00  
Hitachi Tower  
Singapore 0104  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.  
Unit 705, North Tower,  
World Finance Centre  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon  
Hong Kong  
Tel: 27359218  
Fax: 27308074

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